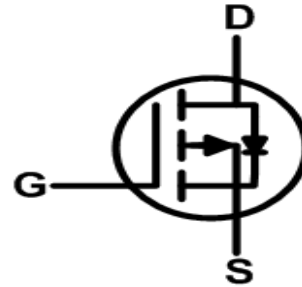




- ★ Super Low Gate Charge
- ★ Green Device Available
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

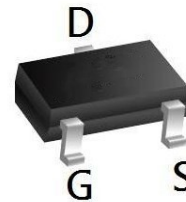


Description

The WL2301B is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The WL2301B meet the RoHS and Green Product requirement with full function reliability approved.

SOT 23 Pin Configurations



Product Summary

BVDSS	RDSON	ID
-20V	93mΩ	-2.0A

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±12	V
$I_D@T_A=25^{\circ}C$	Continuous Drain Current, V_{GS} @ -4.5V ¹	-2.0	A
$I_D@T_A=70^{\circ}C$	Continuous Drain Current, V_{GS} @ -4.5V ¹	-1.4	A
I_{DM}	Pulsed Drain Current ²	-8	A
$P_D@T_A=25^{\circ}C$	Total Power Dissipation ³	0.8	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	156	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	---	°C/W



Electrical Characteristics

$T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
--------	-----------	-----------------	-----	-----	-----	-------

Off Characteristics

BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$	--	--	-1	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$	--	--	-100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$	--	--	100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.45	-0.50	-0.55	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS} = -4.5\text{ V}, I_D = -3.4\text{ A}$	--	93	100	m Ω
		$V_{GS} = -2.5\text{ V}, I_D = -2.5\text{ A}$	--	116	140	

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$	--	267	-	pF
C_{oss}	Output Capacitance		--	30	-	pF
C_{riss}	Reverse Transfer Capacitance		--	28	-	pF

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V},$ (Note 3) $R_G = 3\text{ }\Omega, R_L = 5\text{ }\Omega$	--	10	--	ns
t_r	Turn-On Rise Time		--	6	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	20	--	ns
t_f	Turn-Off Fall Time		--	7	--	ns
Q_g	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -2\text{ A},$ (Note 3) $V_{GS} = -4.5\text{ V}$	--	3.1	--	nC
Q_{gs}	Gate-Source Charge		--	0.5	--	nC
Q_{gd}	Gate-Drain Charge		--	0.8	--	nC
R_G	Gate Resistance	$f = 1\text{ MHz}$	--	6.1	--	Ω

Drain-Source Diode Characteristics and Maximum Ratings

I_S	Maximum Continuous Drain-Source Diode Forward Current	--	--	-2	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current	--	--	-8	A
V_{SD}	Drain to Source Diode Forward Voltage, $V_{GS} = 0\text{ V}, I_{SD} = -3\text{ A}, T_J = 25^\circ\text{C}$	--	--	-1.2	V

Notes:

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Device mounted on FR-4 PCB, 1inch x 0.85inch x 0.062 inch
3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$



Typical Performance Characteristics

P- Channel Typical Characteristics

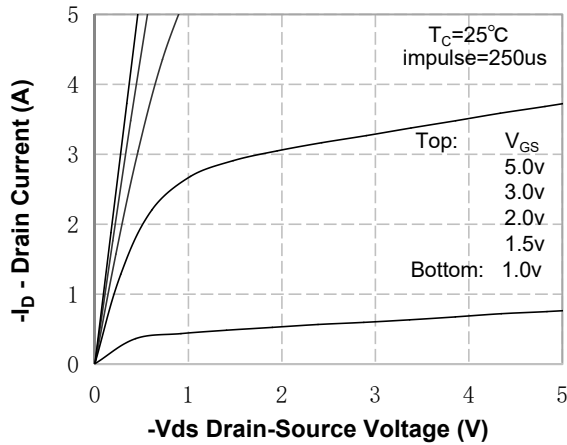


Figure 1. On-Region Characteristics

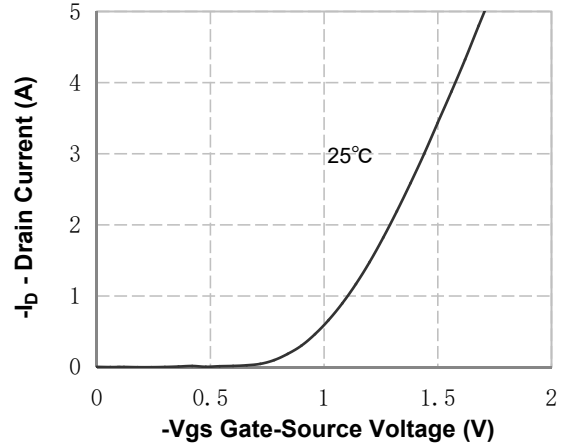


Figure 2. Transfer Characteristics

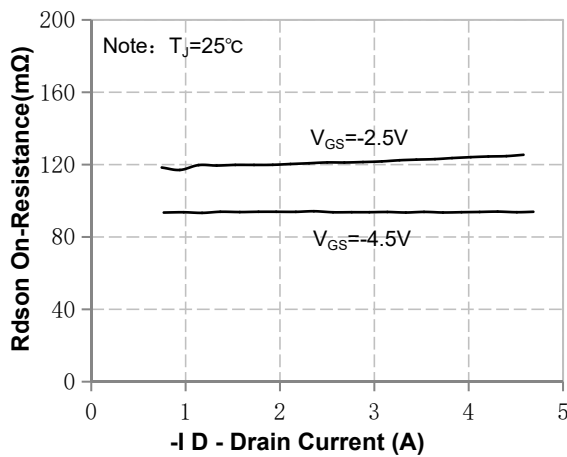


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

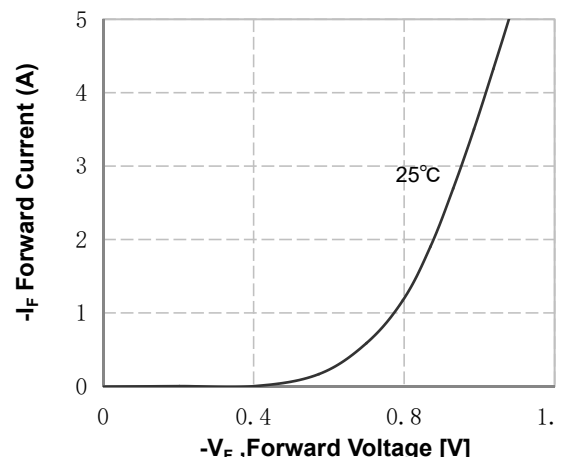


Figure 4. Body Diode Forward Voltage Variation with Source Current

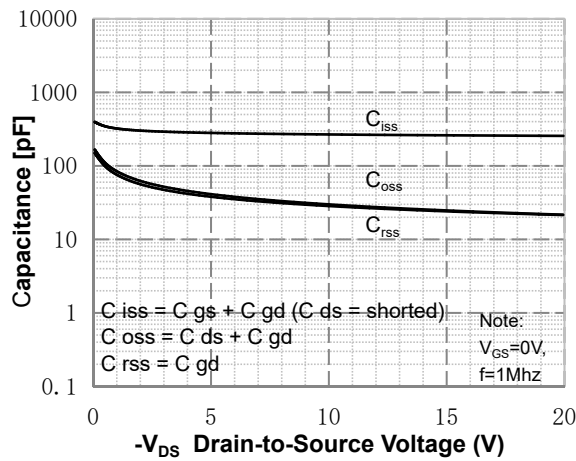


Figure 5. Capacitance Characteristics

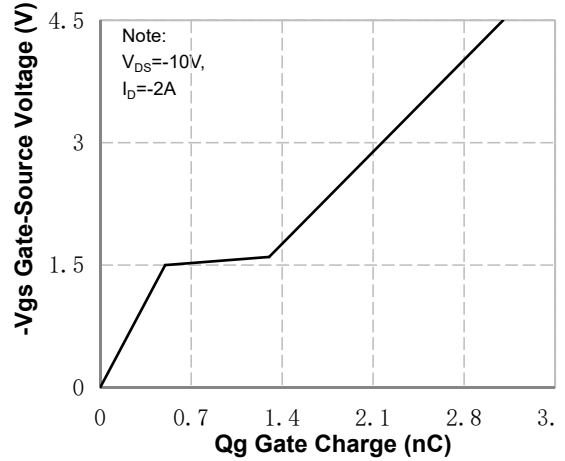


Figure 6. Gate Charge Characteristics



P- Channel Typical Characteristics

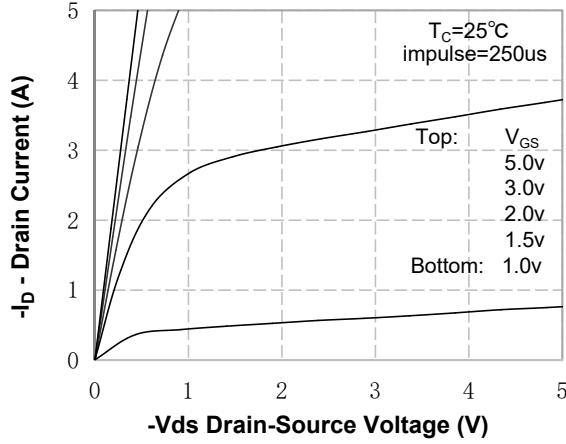


Figure 1. On-Region Characteristics

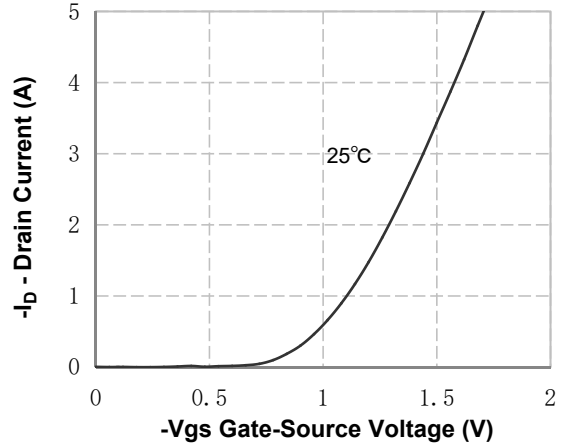


Figure 2. Transfer Characteristics

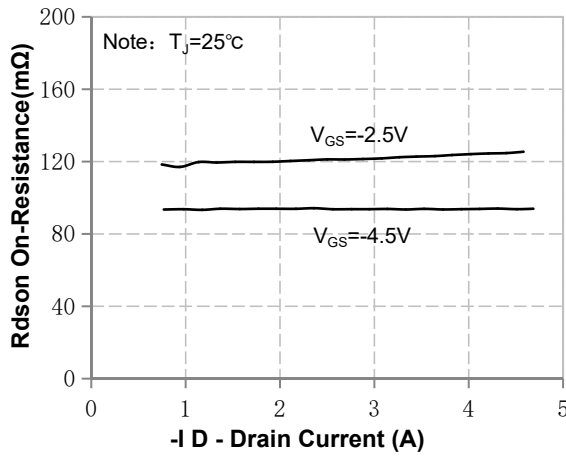


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

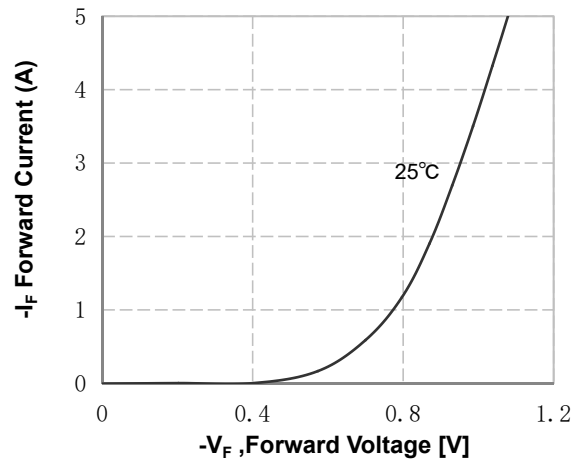


Figure 4. Body Diode Forward Voltage Variation with Source Current

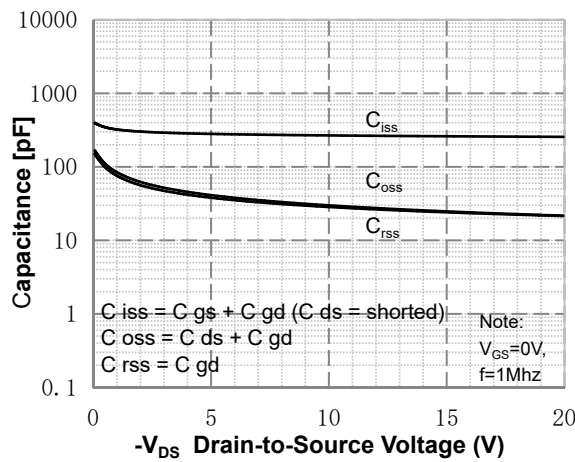


Figure 5. Capacitance Characteristics

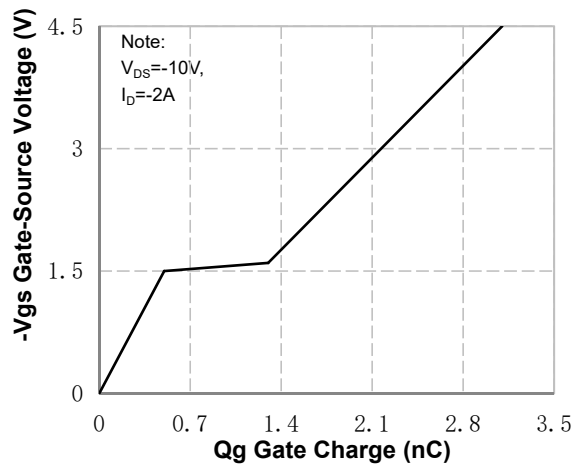
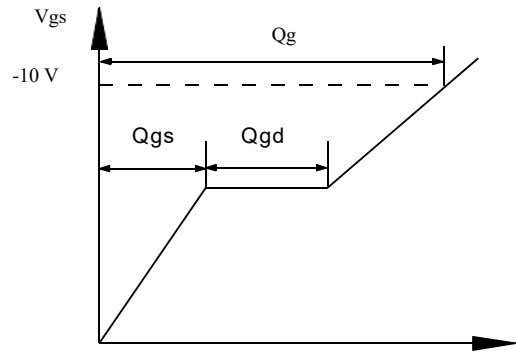
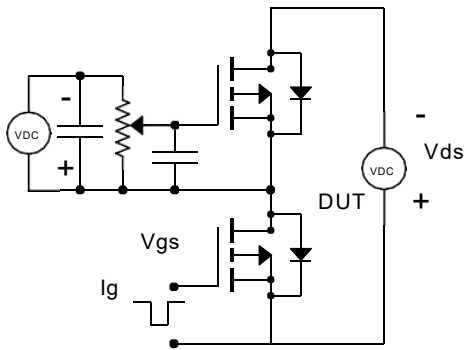


Figure 6. Gate Charge Characteristics

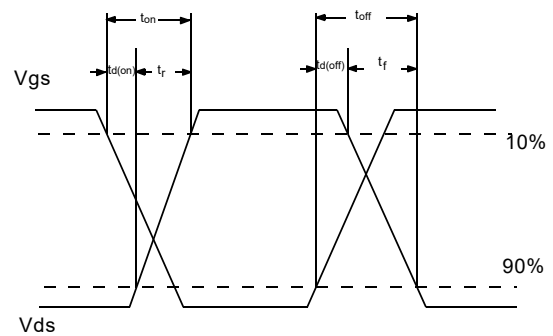
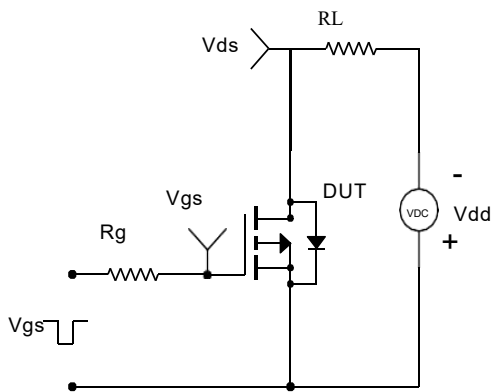


P- Channel

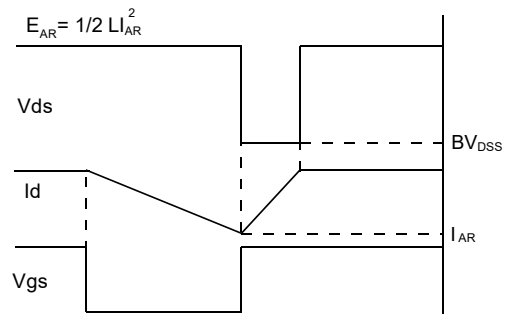
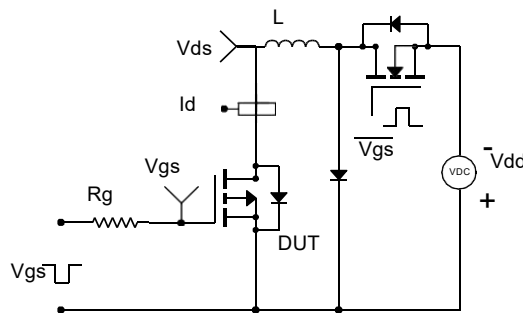
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



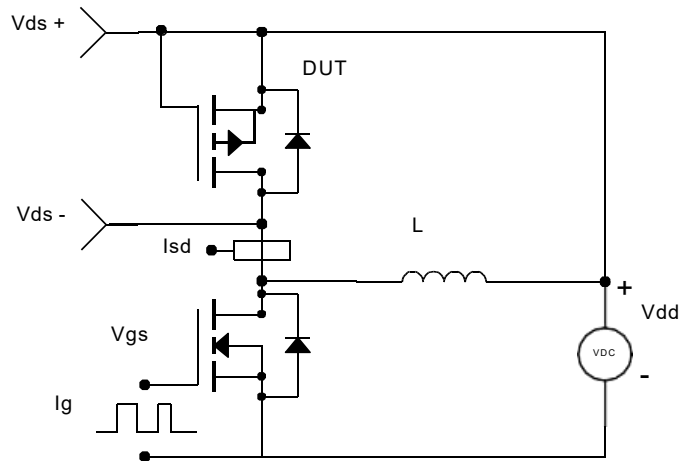
Unclamped Inductive Switching Test Circuit & Waveforms



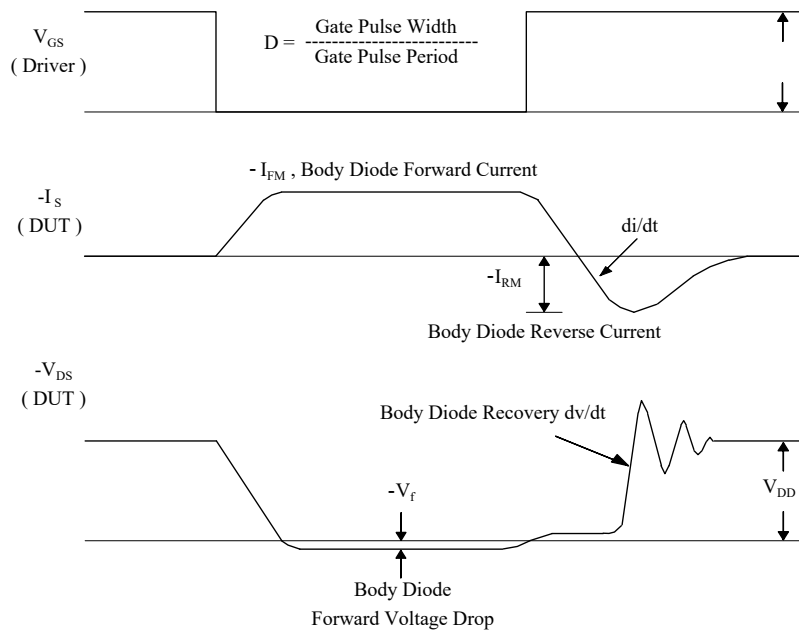


P- Channel

Peak Diode Recovery dv/dt Test Circuit & Waveforms

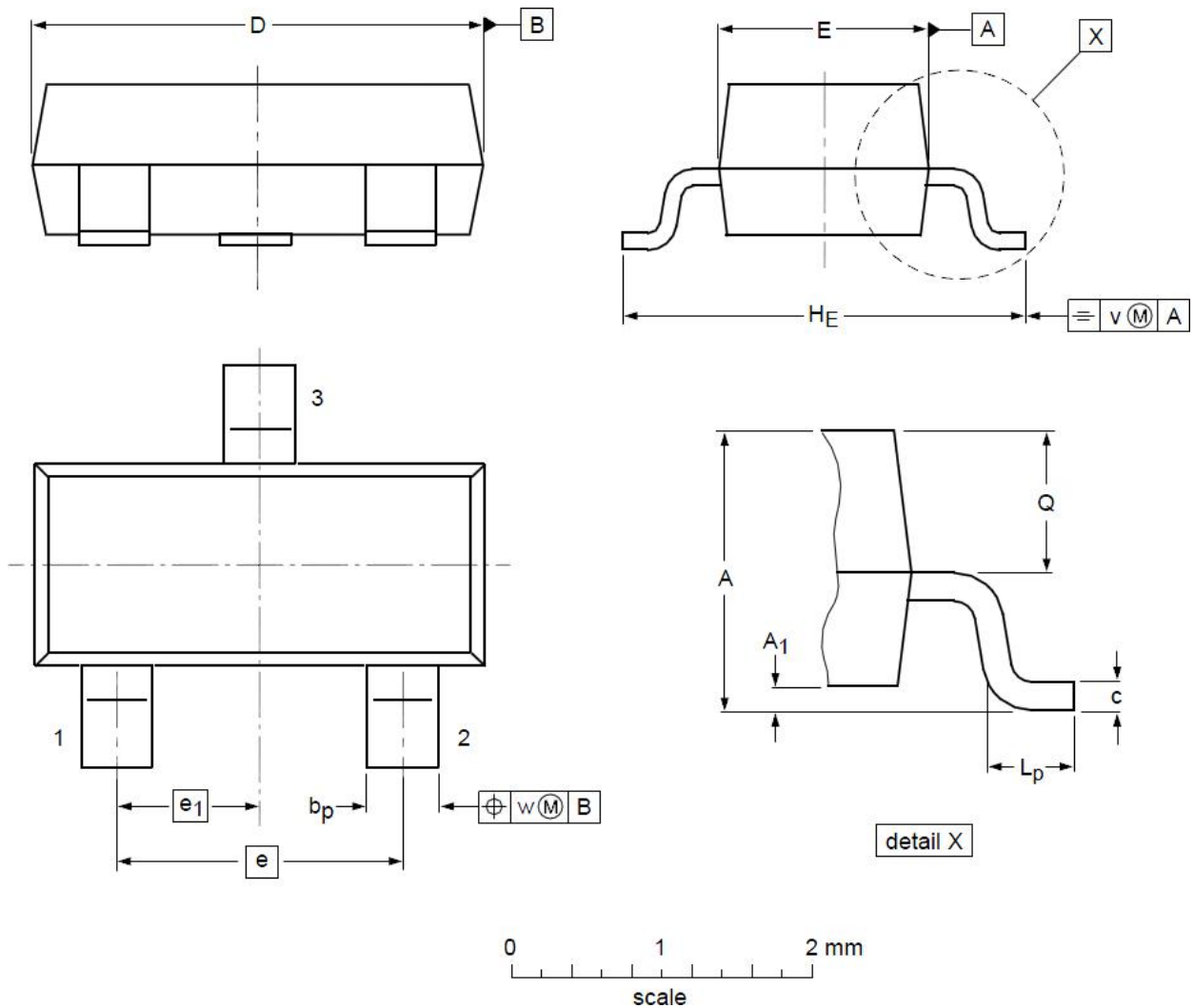


- dv/dt controlled by R_G
- I_{SD} controlled by pulse period





Package Mechanical Data-SOT-23



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A ₁	0.01	0.05	0.10
b _p	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e ₁	--	0.95	--
H _E	2.25	2.40	2.55	L _p	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				



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